

ABSTRACT

Provided are a hard nitride-containing sputtering target that enables preventing the occurrence of arcing during sputtering due to contamination with relatively coarse zirconia particles to suppress the generation of particles during the film formation and a method for producing the hard nitride-containing sputtering target.

A hard nitride-containing sputtering target, including: alloy phases containing Fe or Co, and non-magnetic phases containing a hard nitride selected from AlN, BN, Cr₂N, Si₃N₄, HfN, NbN, TaN, TiN, VN, and any combination thereof, wherein the Zr impurity concentration in the case of the measurement thereof as metal Zr is regulated to 1000 ppm or less, and wherein the Vickers hardness, Hv, measured under a load condition of 3 kgf is 200 or more and 600 or less.